

Form PTO-1449 (Modified)	Atty Docket No. 2013P015	Application No. 10/071,127
List of Patents & Publications Statement	Applicant(s): Il-yong Park, et al.	
(Use several sheets if necessary)	Filing Date: February 08, 2002	Group No.: 2822

U.S. PATENT DOCUMENTS

Exam. Initials		Document Number	Date	Name	Class	Sub-class	Filing Date (if appropriate)
TMT	AA	5,567,634	10/22/1996	Hebert et al.	437	41	
	AB	5,665,619	09/09/1997	Kwan et al.	438	270	
	AC	5,689,128	11/18/1997	Hshieh et al.	257	331	
	AD	5,970,344	10/19/1999	Kubo et al.	438	270	
TMT	AE	6,238,981	05/29/2001	Grebs	438	272	
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

Exam. Initials		Document Number	Date	Country	Class	Sub-class	Translation Yes	No
	AL							
	AM							
	AN							
	AO							
	AP							
	AQ							

OTHER ART (Including Title, Author, Date, Pertinent Pages, etc.)

Exam. Initials		Document Identification
TMT	AR	IEEE 2000, "A 0.03um Trench Gate MOSFET with an ultra low on state resistance and a high destruction immunity during the inductive switching", A. Narazaki, et al., 3 pages
TMT	AS	IEEE 1999, "2.5V-Driven Nch 3rd Generation Trench Gate MOSFET", A Osawa, et al., 4 pages
TMT	AT	2001 International Symposium on Power Semiconductor Devices ICs, "An ultra Dense Trench-Gated Power MOSFET Technology Using a Self-Aligned Process", J. Zeng, et al., 4 pages

Examiner: T. M. Thomas Date Considered: 09-29-04

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication



Form PTO-1449 (Modified)	Atty Docket No. 2013.P015	Application No. 10/071,127
List of Patents & Publications Statement	Applicant(s): Il-yong Park, et al.	
(Use several sheets if necessary)	Filing Date: February 8, 2002	Group No.: 5822

U.S. PATENT DOCUMENTS

Exam. Initials		Document Number	Date	Name	Class	Sub-class	Filing Date (if appropriate)
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

RECEIVED
MAR - 1 2002
TECHNICAL SERVICES DIVISION 2800

FOREIGN PATENT DOCUMENTS

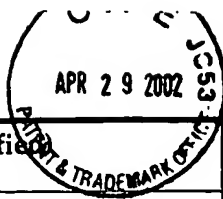
Exam. Initials		Document Number	Date	Country	Class	Sub-class	Translation Yes	No
	AL							
	AM							
	AN							
	AO							
	AP							
	AQ							

OTHER ART (Including Title, Author, Date, Pertinent Pages, etc.)

Exam. Initials		Document Identification
TMT	AR	2001 Elsevier Science, Journal of Alloys and Compounds 323-324, "The blue-phosphor Sr ₂ CeO ₄ synthesized by Pechini's method", O.A. Serra, et al., 3 pages
TMT	AS	2001 International Symposium on Power Semiconductor Devices ICs, "Recessed Trench MOSFET Process Without Critical Alignments Makes Very High Densities Possible", A. Finney, et al., 4 pages
TMT	AT	2001 Elsevier Science Ltd., "A process simplification scheme for fabricating self-aligned silicided trench-gate power MOSFETs", M. Juang, 4 pages

Examiner: T. M. Thomas Date Considered: 09-29-04

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication



Form PTO-1449 (Modified)	Atty Docket No. 2013.P015	Application No. 10/071,127
List of Patents & Publications Statement	Applicant(s): Il-yong Park, et al.	
(Use several sheets if necessary)	Filing Date: February 8, 2002	Group No.: 2822

U.S. PATENT DOCUMENTS

Exam. Initials		Document Number	Date	Name	Class	Sub-class	Filing Date (if appropriate)
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

RECEIVED
MAY - 1 2002
TECHNOLOGY INDEX 2800

FOREIGN PATENT DOCUMENTS

Exam. Initials		Document Number	Date	Country	Class	Sub-class	Translation Yes	No
	AL							
	AM							
	AN							
	AO							
	AP							
	AQ							

OTHER ART (Including Title, Author, Date, Pertinent Pages, etc.)

Exam. Initials		Document Identification
TMT	AR	IEEE 2000, "High-Density Low On-Resistance Trench MOSFETs Employing Oxide Spacers and Self-Align Technique for DC/DC Converter", J. Kim, et al., 4 pages
	AS	
	AT	

Examiner: T. M. Thomas Date Considered: 09-29-04

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication